

Date of Deposit: April 3, 2007

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: NGUYEN et al.

Appln. No.: 10/577,175

Filed: April 26, 2006

For: METHOD FOR SELF-SUPPORTED TRANSFER OF A FINE LAYER BY PULSATION AFTER IMPLANTATION OR CO-IMPLANTATION

Examiner: TBA

Art Unit: TBA

Attorney Docket No: 9905/40 (BIF116533/US)

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Mail Stop Missing Parts
Commissioner for Patents
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In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and more particularly in accordance with 37 C.F.R. §1.97(b), Applicants hereby cite the following reference(s):

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<u>Patent No.</u>	<u>Date</u>	<u>Inventor</u>
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Moriceau et al., [Vol. 99-1] Meeting Abstract No. 405, "A New Characterization Process Used to Qualify SOI Films," *The 195th Meeting of The Electrochemical Society*, May 2-6, 1999, Seattle, Washington

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Wong et al., "Integration of GaN Thin Films with Dissimilar Substrate Materials by Pd-In Metal Bonding and Laser Lift-off", <i>Journal of Electronic Materials</i> , Vol. 28, No. 12, 1999, pp. 1409-1413

Yun et al., "Fractional Implantation Area Effects on Patterned Ion-Cut Silicon Layer Transfer," Dept. of Electrical Eng. And Computer Sciences, University of California, Berkeley, CA 94720, USA, 1999 IEEE International SOI Conference, Oct. 1999, pg. 129-30
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Yun et al., "Thermal and Mechanical Separations of Silicon Layers from Hydrogen Pattern-Implanted Wafers," <i>Journal of Electronic Materials</i> , Vol. No. 36, No. 8 2001

Applicants are enclosing Form PTO-1449 (four sheets), along with a copy of each listed reference for which a copy is required under 37 C.F.R. §1.98(a)(2). As each of the listed references is in English, no further commentary is believed to be necessary, 37 C.F.R §1.98(a)(3). Applicants respectfully request the Examiner's consideration of the above reference(s) and entry thereof into the record of this application.

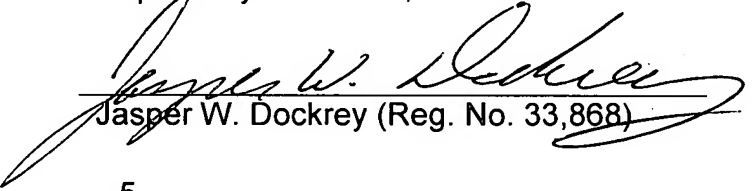
By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

Applicants have calculated no fee to be due in connection with the filing of this Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Statement to a deposit account, as authorized in the Transmittal accompanying this Statement.

Respectfully submitted,

April 3, 2007

Date


Jasper W. Dockrey (Reg. No. 33,868)

FORM PTO-1449	SERIAL NO. 10/577,175	CASE NO. 9905/40
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE April 26, 2006	GROUP ART UNIT Unknown
(use several sheets if necessary)		APPLICANT(S): Nguyen et al.

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER <small>Number-Kind Code (If known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	B1	4,028,149	6/7/1977	Deines et al.		
	B2	4,254,590	3/10/1981	Eisele et al.		
	B3	5,242,863	9/7/1993	Xiang-Zheng et al.		
	B4	5,300,788	4/5/1994	Fan et al.		
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	B7	5,405,802	4/11/1995	Yamagata et al.		
	B8	5,559,043	9/24/1996	Bruel		
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EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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